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# Enhanced photocatalytic performance: a $\beta$ -Bi<sub>2</sub>O<sub>3</sub> thin film by nanoporous surface

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#### Abstract

Beta-Bi<sub>2</sub>O<sub>3</sub> film photoanodes with different surface structures were prepared by oxidizing bismuth films. The physical properties were characterized by x-ray diffraction (XRD), scanning electron microscopy (SEM), UV–visible absorbance spectra and atomic force microscopy (AFM). XRD shows that all films are beta phase crystal structure except the thinnest 12 nm film. SEM and AFM characterizations indicate that a nanoporous surface structure is generated on the surface after the film is annealed for 3 h, while the films annealed for 1 h show a dense surface. The direct band gaps vary from 2.63 to 2.88 eV, with the film thickness decreasing from 500 to 12 nm. The nanoporous surface structure film exhibits better light harvesting ability and incident photon-to-electron conversion efficiency (IPCE) than the dense surface films. The IPCE (61% at 350 nm and 43% at 400 nm, 0.197 V<sub>NHE</sub>) is the highest ever reported. The photocurrent density reaches 0.45 mA cm<sup>-2</sup> when illuminated with a bias of 1.23 V<sub>NHE</sub> in 0.5M Na<sub>2</sub>SO<sub>3</sub>.

(Some figures may appear in colour only in the online journal)

# 1. Introduction

Direct photo-decomposition of water by semiconductor photocatalysts into hydrogen and oxygen is a promising way to produce clean and renewable energy. Since Fujishima and Honda [1] discovered the water splitting effect by illuminating a TiO<sub>2</sub> electrode under UV irradiation, a large number of studies have been carried out to find suitable materials. However, most of the experiments failed to obtain the conversion efficiency for commercial use. There were four essential requirements [2,3] for the material to photo-decompose water into H<sub>2</sub> and O<sub>2</sub>. In recent years, bismuth vanadate and bismuth tungstate,  $BiVO_4$  [4] and  $Bi_2WO_6$  [5], have been paid considerable attention in many studies. However, pure  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> is an important metaloxide-semiconductor with a direct band gap of 2.8 eV. Its photocatalytic activity corresponds to visible light, [6, 7]. Due to the good charge mobility of  $\beta$ -Bi<sub>2</sub>O<sub>3</sub>, excited electrons and holes could have relatively long lives. Thus, they could be separated easily under specific conditions. The recombination inside the film could be reduced ultimately. So far, many different  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> photocatalysts have been reported. Harriman et al [8] prepared the solid solutions of Bi<sub>2</sub>O<sub>3</sub> and Nb<sub>2</sub>O<sub>5</sub> crystallize and the material could photodecompose chlorinated hydrocarbons. Zhang et al [9] reported that sonochemically synthesized monoclinic nanocrystallite  $Bi_2O_3$  ( $E_g = 2.85 \, eV$ ) could degrade 86% of methyl orange within 100 min under visible light illumination. Kim et al [10] fabricated a  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> thin film on Au-coated Si substrates by means of metal organic chemical vapour deposition (MOCVD). A one-dimensional structure was formed at a low temperature of 400 °C with a diameter of about 30–90 nm.  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> nanofibres [11] were prepared by electro-spinning a precursor mixture of polyacrylonitrile/bismuth-nitrate and then annealing at different temperatures. The photo-activity was high for photo-degradation of Rhodamine B and the photoactivity did not decrease after illumination. Brezesinski et al [12] synthesized cubic mesoporous  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> thin films ( $E_g$  = 2.85 eV) by coassembly of hydrated bismuth nitrate with the poly-(ethylene-co-butylene )-block-poly( ethylene oxide) diblock copolymer. For improving the structural stability of  $\beta$ -Bi<sub>2</sub>O<sub>3</sub>, Wang *et al* [13] doped  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> with titanium by the hydrothermal method. After photo-degradation of

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three kinds of dyes, the Ti-doped  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> was still chemical stable. Huang et al [5] compared the photo-activity between  $\alpha$ -Bi<sub>2</sub>O<sub>3</sub> and  $\beta$ -Bi<sub>2</sub>O<sub>3</sub>. The  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> showed narrower band gap with better light harvesting ability in the visible region, which resulted in a higher photocatalytic activity. Zhu et al [14] determined that 2.0 wt% Ag-doped  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> showed the best photo-activity by degradation of Rhodamine B.  $Ag/\beta$ -Bi<sub>2</sub>O<sub>3</sub> structure was good for the migration of the electronhole pairs, resulting in a higher visible light photocatalytic activity. Qiu et al [15] investigated the growth conditions of nanowires systematically. The  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> nanowires had better photo-degradation ability than  $\alpha$ -Bi<sub>2</sub>O<sub>3</sub>. Moniz [16] reported that the  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> prepared by low-pressure chemical vapour deposition (LPCVD) had a band gap of about 2.3-3.0 eV. When illuminated, O2 was oxidized from water and the calculated quantum yield efficiency (QE) was about 9.8% at 365 nm.

We mainly studied how the nanoporous surface structure affects the photo-activity in this experiment. The relationship between the film thickness and photoelectrochemical property was also assessed. We discovered that the photo-activity of the porous surface film was twice as high as the dense surface film. We also obtained the highest photon-to-electron conversion efficiency (IPCE) (61% at 350 nm and 43% at 400 nm, respectively) for  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> material.

# 2. Experiment

#### 2.1. Thin film preparation

Bismuth films of different thicknesses were deposited by a radio frequency magnetron sputtering system on FTO conductive glass (TEC 15, 14  $\Omega$ /square, 25 × 25 mm<sup>2</sup>). Pure bismuth (99.99%) was used as the sputtering target. One edge of the FTO surface was covered by a polyimide tape, which was used for the photoelectrochemical testing contact later. The base vacuum was  $8.0 \times 10^{-4}$  Pa, the argon flow was kept at 30 sccm, and the sputtering power was 20 W. The depositing time was 5 min (sample no 1), 40 min (sample no 2 and no 3) and 90 min (sample no 4), respectively (table 1). The 40 min sample was cut into two pieces and marked as sample no 2 and sample no 3. Sample no 1 and no 2 were annealed at 250 °C in air for 1 h to turn the metal into pure metal oxide. Sample no 3 and no 4 were annealed for 3 h at 250 °C in air to obtain the nanoporous surface structure.

#### 2.2. Physical characterizations

Film thickness was measured by Alpha-Step D-100. The surface structure was characterized by an S-4800 scanning electron microscope and a CSPM-4000 model atomic force microscope. XRD was used to characterize the phase state in the scanning range  $20^{\circ}-70^{\circ}$  ( $2\theta$ ) (Cu K $\alpha_1$  radiation,  $\lambda = 1.54056$  Å, 40 kV, 25 mA). UV–visible absorbance spectra were measured to study the light harvesting ability. Clean blank FTO glass was used as the standard baseline.



**Figure 1.** XRD patterns of  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> thin films.

#### 2.3. IPCE and APCE measurements

The IPCE measurements were carried out in a self-made vessel fitted by quartz window in 1.0M NaOH solution. The system was made of an SBP500 monochromator, a potentiostat, a lock-in amplifier and one 150 W xenon lamp. A graphite rod was used as the counter electrode, and Ag/AgCl (saturated KCl solution) as the reference electrode in all experiments. The relationship between NHE and the Ag/AgCl reference electrode is  $E_{\text{NHE}} = E_{\text{Ag/AgCl}} + 0.197 \text{ V}$  [17].

## 2.4. Photocurrent test

The photocurrent data were collected by solartron 1287 and 1260 electrochemical interface in 0.5M  $Na_2SO_3$  solution. Illuminating light source was a 150 xenon lamp with an AM 1.5 filter. The light intensity was 60 mW cm<sup>-2</sup> measured by a sun meter.

## 3. Results and discussion

#### 3.1. X-ray diffraction

XRD was used to identify the crystal phase of samples. Figure 1 reveals that all films exhibit pure  $\beta$ -phase except the 12 nm film (tetragonal, JCPDS card No 27-0050) and there are no other phases ( $\alpha$ - or  $\delta$ - Bi<sub>2</sub>O<sub>3</sub>). The (2 0 1) peak position of the 12 nm sample is varied from the standard (2 0 1) line,

The diffraction density becomes stronger with increasing film thickness. The thinnest 12 nm film shows a weak (201) peak and there are no obvious diffraction peaks of  $\beta$ -Bi<sub>2</sub>O<sub>3</sub>, while the other three films have good crystallinity after annealing. The samples exhibit pre-orientation in the (201) direction. The calculated unit cell dimensions of a = b = 7.7 Å and c = 5.7 Å are in agreement with reference values (a = b = 7.741 Å, c = 5.634 Å) [18]. The grain size of the film is calculated by Debye–Scherrer's formula [19, 20]:

$$D = \frac{K\lambda}{(\beta\cos\theta)},$$

where D is the crystallite mean dimension, K is the Scherrer constant (K = 0.94),  $\lambda$  is the wavelength of Cu K $\alpha_1$ ,  $\beta$  is



**Figure 2.** SEM images of  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> thin films: (*a*) 12 nm, dense surface; (*b*) 200 nm, dense surface; (*c*) 210 nm, nanoporous surface; (*d*) 500 nm, nanoporous surface with accumulated tiny grains. Length scale: 1 $\mu$ m.



**Figure 3.** UV–visible absorption spectra (*a*), IPCE (*b*) and APCE (*c*) of  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> films.

the full-width at half-maximum and  $\theta$  is the Bragg diffraction angle. The calculation is based on the (201) peak. The estimated grain sizes are listed in table 1.

#### 3.2. Surface morphology

The surface structures of the four samples are shown in figure 2. The 12 nm film (figure 2(a)) shows a densely arranged surface and the particles grow on the surface of SnO<sub>2</sub>, so it is difficult to identify the grain size from XRD data. A large number of nano-polygon particles (50–150 nm) are formed on the other three film surfaces. As the film thickness increases, tiny grains aggregates with each other and finally form bigger particles. There is a lot of empty space among those particles in figures 2(c) and (d). But figure 2(c) has better crystallinity than figure 2(d), because there are many tiny particles accumulated around bigger particles on the surface accompanied by more drawbacks. Figures 2(b) and (c) were made from the same bismuth sample but the annealing time was different. So the porous surface was generated during the annealing process. Many small crystal particles are formed enclosing larger particles in figure 2(d). The reason may be that there is inadequate annealing time for the grains to grow into large crystals. Figure 2(b) shows that the surface structure of the 200 nm sample (annealed for 1 h) is a dense surface. The nanoporous surface structure enables the electrolyte to permeate into the surface, reacting with the photogenerated holes directly on the particle surface. So, the porous surface could potentially promote the charge transfer process [21–23, and eventually increase PEC efficiency.

#### 3.3. UV-visible absorbance spectra

The UV–visible absorbance spectra of each sample are shown in figure 3. The derived energy gap of the  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> films are based on the Tauc formula (figure 4) [24, 25]:

$$(\eta h \upsilon)^2 \propto A(h \upsilon - E_g).$$

Sample no	Annealing time (h)	Thickness (nm)	(201) FWHM (°)	Grain size (nm)	E <sub>g</sub> (eV)	Surface structure
1 2 3 4	1 1 3 3	12 200 210 500	Undefined 0.205 0.204 0.186	Undefined 45 44 48	$\begin{array}{c} 2.88 \pm 0.02 \\ 2.83 \pm 0.03 \\ 2.75 \pm 0.02 \\ 2.63 \pm 0.02 \end{array}$	Dense Dense Porous Porous

**Table 1.** Physical properties of Bi<sub>2</sub>O<sub>3</sub> films.



**Figure 4.** Direct band transition fitting versus photon energy of  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> thin films: (*a*) 12 nm film, (*b*) 200 nm dense film, (*c*) 210 nm nanoporous film, (*d*) 500 nm film.

Here, the quantum efficiency,  $\eta$ , is proportional to the square root of the photon energy under direct transition condition. *A* is the proportionality constant, *hv* is the photon energy and  $E_g$  is the energy gap. The calculated energy gap is listed in table 1.

The direct energy gaps of the four samples are in accordance with George's report [26] but narrower than the  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> nanowires reported [12]. Figure 4 indicates that the band gap decreases with increasing film thickness. The 12 nm film has the widest energy gap of 2.88 eV because of its nanosize effect. The nanoporous surface film shows better photoabsorbance and narrower  $E_g$  than those of the dense surface film, because the empty space on its surface could reflect the incident light and then the adjacent particles can absorb the reflected light, which improves the light absorbing process eventually (figure 5(*d*)). As a visible light photocatalyst candidate, the 500 nm film extends the absorbance edge to 470 nm, which means it could utilize more sunlight.

# 3.4. IPCE and APCE

The induced IPCE is defined as

$$IPCE = \frac{I}{P} \frac{1240}{\lambda} \times 100\%,$$

where I is the photocurrent density  $(mA cm^{-2})$ . P is the power of the monochromatic light irradiated on the electrode  $(mW cm^{-2})$  and  $\lambda$  is the wavelength (nm). The measurements are carried out under  $0.197 V_{NHE}$  (figure 3(b)). All films exhibit good photo-activity in the visible light region ( $\lambda \ge 400$  nm). The 210 nm film exhibits the highest IPCE at 350 nm and 400 nm, which is 61% and 43%, respectively. The IPCE of the 210 nm sample is almost six times that of the reported bismuth oxide thin films prepared by MOCVD [16].  $\beta$ -phase Bi<sub>2</sub>O<sub>3</sub> has an intermediate conductivity between the  $\alpha$ - and  $\delta$ -phase. So there are three advantages for the 210 nm nanoporous film. First, it has a narrow energy gap of about 2.73 eV, which means it could harvest more visible light photons than the thinner sample and ultimately induce more electrons and Second, it shows the best crystallinity among the holes. four samples, which contributes to its conductivity. Most of the photogenerated electrons could move to the back contact electrode (FTO) rather than recombining with holes in the bulk film and hence reduce the recombination inside the film. Since the particles in the 200 nm films are not as big as the particles in the 210 nm film, the photoelectrochemical performance of the 200 nm film is lower than that of the 210 nm one. Although the 500 nm film had better light absorption ability, it could not obtain better photoelectrochemical performance



**Figure 5.** AFM surface structure (*a*), three-dimensional image (*b*), section analysis (*c*) and Schematic diagram of the photoelectrochemical processes (*d*) in the 210 nm nanoporous surface film.

than the 210 nm film, owing to its surface defects. Third, the nanoporous surface structure of the 210 nm film allows the electrolyte to permeate to the empty space among the particles and enlarge the contact area between particles and electrolyte. Therefore, photogenerated holes on the surface could react with OH<sup>-</sup> ions in the electrolyte directly, which also finally reduced the recombination on the surface. Figures 5(a), (b) and (c) show the surface structure, three-dimensional surface and section analysis of the red rectangle marked area of the 210 nm film. The surface structure analysis conforms to the former assumptions.

Some researchers had also fabricated  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> thin films; however, most of them failed to contain the three advantages at the same time. So the photoelectrochemical performance was not as ideal as the samples in this experiment. Based on Hameed's [27] work, the 210 nm film may be a composite of  $Bi_2O_3$  and  $Bi_2O_{4-x}$ . Among all the oxidizing species, superoxide radical has the highest oxidation power and the sufficiently long lifetime. So the photogenerated holes on the film surface could live long and then move to the reactive site on the surface. The photocurrent density is shown in figures 6(a) and (b). Here the onset potential of all the films is located at  $-0.15V_{\text{NHE}}$ , in 0.5M Na<sub>2</sub>SO<sub>3</sub> solution. The photocurrent density of nanoporous 210 nm film reaches  $0.45 \text{ mA cm}^{-2}$  under  $1.23 \text{V}_{\text{NHE}}$ , while that of the 200 nm film with dense surface reaches only  $0.04 \text{ mA cm}^{-2}$  at  $1.23 V_{\text{NHE}}$ . So the photoelectrochemical property is increased strongly by the nanoporous structure.

The absorbed photon-to-current efficiency (APCE) of the four samples is shown in figure 3(c). APCE is defined by the formula [10]

$$APCE = \frac{IPCE}{1 - 10^{-A}}$$

Here A is the absorbance.  $(1 - 10^{-A})$  represents the light harvesting efficiency (LHE) of the film. Owing to the nanoporous surface structure, the light is reflected between the crystal grains and the electrolyte on the surface rather than passing through the film directly on the dense film surface, which could relatively enlarge the photon absorbing ability. And the 210 nm film still possesses the highest APCE. The IPCE of the 12 nm film is 20% at 350 nm; however, the APCE is 30%, so more than half of the light is wasted when the light passes through the film. The 200 nm film with a dense surface shows smaller absorbance than the 210 nm film with a nanoporous surface. The 500 nm film is very thick, so the photogenerated electrons and holes cannot have enough time to pass through the film bulk and ultimately recombine with each other in the film. The APCE curve of 210 nm film decays smoothly ( $\lambda < 450$  nm), which suggests that it has the best thickness among four films.

#### 4. Conclusions

A series of highly photoactive  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> films were fabricated on FTO substrates. A  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> film with a nanoporous surface structure is generated by prolonging the annealing time. The particle size of the 210 nm film is bigger than the other three films, and there are fewer small particles generated on the surface than the thick 500 nm film. The prepared films with varied thickness show different photo-response and photoelectrochemical performance. IPCE and APCE analyses indicate that the 210 nm film with a nanoporous surface shows the highest photoelectrochemical activity at a bias of 0.197V<sub>NHE</sub>, because it possesses three advantages (effective light harvesting ability, good crystallinity and nanoporous



Figure 6. *I*–*V* plots of dense 200 nm surface and 210 nm nanoporous surface films (*a*); dense surface 12 and 500 nm films (*b*).

surface structure) to reduce bulk and surface recombination at the same time. From the comparison with dense and nanoporous surface structures, we discover that the nanoporous surface could promote the photoelectrochemical property of  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> strongly.

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#### References

- [1] Fujishima A and Honda K 1972 Nature 238 37-8
- [2] Chen X B, Shen S H, Guo L J and Mao S S 2010 Chem. Rev. 110 6503–70
- [3] Lian X, Yang X, Liu S, Xu Y, Jiang C, Chen J and Wang R 2012 Appl. Surf. Sci. **258** 2307–11
- [4] Iwase A and Kudo A 2010 J. Mater. Chem. 20 7536-42
- [5] Huang Q Q, Zhang S N, Cai C X and Zhou B 2011 Mater. Lett.
  65 988–90
- [6] Maruthamuthu P, Gurunathan K, Subramanian E and Sastri M V C 1993 Int. J. Hydrogen Energy 18 9–13
- [7] Maruthamuthu P, Gurunathan K, Subramanian E and Sastri M V C 1994 Int. J. Hydrogen Energy 19 889–93
- [8] Harriman A, Thomas J M, Zhou W and Jefferson D A 1988 J. Solid State Chem. 72 126–30
- [9] Zhang L S, Wang W Z, Yang J O, Chen Z G, Zhang W Q, Zhou L and Liu S W 2006 Appl. Catal. A 308 105–10

- [10] Kim H W, Lee J W, Shim S H, Kebede M A and Lee C 2008 Cryst. Res. Technol. 43 695–9
- [11] Wang C H, Shao C L, Wang L J, Zhang L, Li X H and Liu Y C 2009 J. Colloid Interfce Sci. 333 242–8
- [12] Brezesinski K, Ostermann R, Hartmann P, Perlich J and Brezesinski T 2010 Chem. Mater. 22 3079–85
- [13] Wang Y, Wen Y Y, Ding H M and Shan Y K 2010 J. Mater. Sci. 45 1385–92
- [14] Zhu G Q, Que W X and Zhang J 2011 J. Alloys Compounds 509 9479–86
- [15] Qiu Y F, Yang M L, Fan H B, Zuo Y Z, Shao Y Y, Xu Y J, Yang X X and Yang S H 2011 *Crystengcomm* **13** 1843–50
- [16] Moniz S J A, Blackman C S, Carmalt C J and Hyett G 2010 J. Mater. Chem. 20 7881–6
- [17] Reece S Y, Hamel J A, Sung K, Jarvi T D, Esswein A J, Pijpers J J H and Nocera D G 2011 *Science* **334** 645–8
- [18] Blower S K and Greaves C 1988 Acta Crystallogr. C 44 587–9
- [19] Patterson A L 1939 Phys. Rev 56 978-82
- [20] Gariné G, Fernando E, Carlos J P, Ricardo E M, Francisco M, Dietmar L, José R R-B and Enrique A D 2012 J. Phy. D: App Phys. 45 245301
- [21] Aroutiounian V M, Arakelyan V M and Shahnazaryan G E 2005 Sol. Energy 78 581–92
- [22] Perez M A and Teijelo M L 2005 J. Electroanal. Chem. 583 212–20
- [23] Wu Z F, Huang F Z, Shen Y H, Xie A J and Song X Q 2011 J. Nanopart. Res. 13 4575–82
- [24] Tauc J 1967 Science 158 1543-8
- [25] Shaban Y A and Khan S U M 2008 Int. J. Hydrogen Energy 33 1118–26
- [26] George J, Pradeep B and Joseph K S 1987 Phys. Status Solidi a 103 607–12
- [27] Hameed A, Montini T, Gombac V and Fornasiero P 2008 J. Am. Chem. Soc. 130 9658–9